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273
papers

7,212
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47
h-index

70
g-index

284
ext. papers

7,686
ext. citations

3
avg, IF

5.41
L-index

#	Paper	IF	Citations
273	Low-power non-volatile spintronic memory: STT-RAM and beyond. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 074003	3	308
272	Observation of magnetic-field-induced delocalization: Transition from Anderson insulator to quantum Hall conductor. <i>Physical Review Letters</i> , 1993 , 71, 1439-1442	7.4	152
271	Switching current reduction using perpendicular anisotropy in CoFeB/MgO magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2011 , 98, 112507	3.4	151
270	Experimental proof-of-principle investigation of enhanced Z3DT in (001) oriented Si/Ge superlattices. <i>Applied Physics Letters</i> , 2000 , 77, 1490-1492	3.4	151
269	Controlled arrangement of self-organized Ge islands on patterned Si (001) substrates. <i>Applied Physics Letters</i> , 1999 , 75, 2752-2754	3.4	132
268	Ultra-low switching energy and scaling in electric-field-controlled nanoscale magnetic tunnel junctions with high resistance-area product. <i>Applied Physics Letters</i> , 2016 , 108, 012403	3.4	131
267	High-mobility p-channel metal-oxide-semiconductor field-effect transistor on strained Si. <i>Applied Physics Letters</i> , 1993 , 62, 2853-2855	3.4	123
266	Raman spectroscopy of electrochemically self-assembled CdS quantum dots. <i>Applied Physics Letters</i> , 2000 , 76, 137-139	3.4	120
265	Measurements of anisotropic thermoelectric properties in superlattices. <i>Applied Physics Letters</i> , 2002 , 81, 3588-3590	3.4	118
264	Optical transitions in a step quantum well. <i>Journal of Applied Physics</i> , 1989 , 65, 4377-4381	2.5	110
263	Wet oxidation of GeSi strained layers by rapid thermal processing. <i>Applied Physics Letters</i> , 1990 , 57, 369-371	3.4	110
262	Si _{1-x} Ge _x /Si multiple quantum well infrared detector. <i>Applied Physics Letters</i> , 1991 , 59, 2588-2590	3.4	102
261	Simultaneous measurements of Seebeck coefficient and thermal conductivity across superlattice. <i>Applied Physics Letters</i> , 2002 , 80, 1758-1760	3.4	93
260	Changes in luminescence emission induced by proton irradiation: InGaAs/GaAs quantum wells and quantum dots. <i>Applied Physics Letters</i> , 2000 , 76, 2074-2076	3.4	91
259	Low writing energy and sub nanosecond spin torque transfer switching of in-plane magnetic tunnel junction for spin torque transfer random access memory. <i>Journal of Applied Physics</i> , 2011 , 109, 07C720	2.5	87
258	Intersubband absorption in boron-doped multiple Ge quantum dots. <i>Applied Physics Letters</i> , 1999 , 74, 185-187	3.4	87
257	In-plane lattice thermal conductivity of a quantum-dot superlattice. <i>Journal of Applied Physics</i> , 2000 , 88, 696-699	2.5	86

256	Regimented placement of self-assembled Ge dots on selectively grown Si mesas. <i>Applied Physics Letters</i> , 2000 , 76, 3591-3593	3.4	85
255	Microscopic structure of interfaces in Si _{1-x} Ge _x /Si heterostructures and superlattices studied by x-ray scattering and fluorescence yield. <i>Physical Review B</i> , 1993 , 47, 16373-16381	3.3	82
254	Rapid thermal oxidation of GeSi strained layers. <i>Applied Physics Letters</i> , 1990 , 56, 66-68	3.4	82
253	Intersubband optical absorption in coupled quantum wells under an applied electric field. <i>Physical Review B</i> , 1988 , 38, 8377-8382	3.3	82
252	Epitaxial growth of high mobility Bi ₂ Se ₃ thin films on CdS. <i>Applied Physics Letters</i> , 2011 , 98, 242102	3.4	79
251	Deep subnanosecond spin torque switching in magnetic tunnel junctions with combined in-plane and perpendicular polarizers. <i>Applied Physics Letters</i> , 2011 , 98, 102509	3.4	76
250	Resonant tunneling through a Si/GeSi _{1-x} /Si heterostructure on a GeSi buffer layer. <i>Applied Physics Letters</i> , 1988 , 53, 204-206	3.4	72
249	Intersubband absorption in Si _{1-x} Ge _x /Si multiple quantum wells. <i>Applied Physics Letters</i> , 1990 , 57, 2585-2587	3.4	71
248	Determination of interface and bulk-trap states of IGFETs using deep-level transient spectroscopy. <i>Journal of Applied Physics</i> , 1976 , 47, 4574-4577	2.5	71
247	Giant voltage modulation of magnetic anisotropy in strained heavy metal/magnet/insulator heterostructures. <i>Physical Review B</i> , 2015 , 92,	3.3	69
246	Magnetically doped semiconducting topological insulators. <i>Journal of Applied Physics</i> , 2012 , 112, 063912	2.5	69
245	Chemical Etching of Si _{1-x} Ge _x in HF : H ₂ O ₂ : CH ₃ COOH. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 1260-1266	3.9	67
244	Nanometer scale patterning of silicon (100) surfaces by an atomic force microscope operating in air. <i>Applied Physics Letters</i> , 1994 , 64, 2133-2135	3.4	66
243	Normal incidence infrared detector using p-type SiGe/Si multiple quantum wells. <i>Applied Physics Letters</i> , 1992 , 60, 103-105	3.4	65
242	A surfactant-mediated relaxed Si _{0.5} Ge _{0.5} graded layer with a very low threading dislocation density and smooth surface. <i>Applied Physics Letters</i> , 1999 , 75, 1586-1588	3.4	62
241	Intervalence-subband transition in SiGe/Si multiple quantum wells—normal incident detection. <i>Applied Physics Letters</i> , 1992 , 61, 681-683	3.4	62
240	Large Stark shifts of the local to global state intersubband transitions in step quantum wells. <i>Applied Physics Letters</i> , 1990 , 56, 1986-1988	3.4	60
239	Formalism of the Kronig-Penney model for superlattices of variable basis. <i>Physical Review B</i> , 1988 , 38, 13307-13315	3.3	60

- 238 Interdiffusion in a symmetrically strained Ge/Si superlattice. *Applied Physics Letters*, **1989**, 54, 1253-1255. 3.4 59
- 237 Electron mobility enhancement from coupled wells in delta-doped GaAs. *Applied Physics Letters*, **1993**, 62, 504-506. 3.4 57
- 236 Giant negative magnetoresistance of a degenerate two-dimensional electron gas in the variable-range-hopping regime. *Physical Review B*, **1992**, 46, 12830-12833. 3.3 57
- 235 Novel infrared band-aligned superlattice laser. *Applied Physics Letters*, **1987**, 51, 1404-1406. 3.4 54
- 234 Normal-incidence strained-layer superlattice Ge_{0.5}Si_{0.5}/Si photodiodes near 1.3 μm . *Applied Physics Letters*, **1995**, 67, 566-568. 3.4 53
- 233 Wet oxidation of GeSi at 700 $^{\circ}\text{C}$. *Journal of Applied Physics*, **1992**, 71, 4015-4018. 2.5 52
- 232 Defect distribution near the surface of electron-irradiated silicon. *Applied Physics Letters*, **1978**, 33, 547-548. 3.4 51
- 231 Optical and acoustic phonon modes in self-organized Ge quantum dot superlattices. *Applied Physics Letters*, **2000**, 76, 586-588. 3.4 50
- 230 Damage and strain in epitaxial Ge_xSi_{1-x} films irradiated with Si. *Journal of Applied Physics*, **1993**, 74, 6039-6045. 3.4 49
- 229 Band structure and symmetry analysis of coherently grown Si_{1-x}Ge_x alloys on oriented substrates. *Physical Review B*, **1993**, 47, 1936-1953. 3.3 49
- 228 Observation of large oscillator strengths for both 1- \rightarrow 2 and 1- \rightarrow 3 intersubband transitions of step quantum wells. *Applied Physics Letters*, **1990**, 56, 1046-1048. 3.4 48
- 227 Towards Si_{1-x}Ge_x quantum-well resonant-state terahertz laser. *Applied Physics Letters*, **2001**, 79, 3909-3911. 3.4 47
- 226 Thermoelectric figure of merit enhancement in a quantum dot superlattice. *Nanotechnology*, **2000**, 11, 327-331. 3.4 47
- 225 Hole intersubband absorption in δ -doped multiple Si layers. *Applied Physics Letters*, **1991**, 58, 1083-1085. 3.4 45
- 224 High-quality Bi₂Te₃ thin films grown on mica substrates for potential optoelectronic applications. *Applied Physics Letters*, **2013**, 103, 031605. 3.4 44
- 223 Tunnel diodes fabricated from CdSe nanocrystal monolayers. *Applied Physics Letters*, **1999**, 74, 317-319. 3.4 43
- 222 Raman scattering from a self-organized Ge dot superlattice. *Applied Physics Letters*, **1999**, 74, 1863-1865. 3.4 43
- 221 Interdiffusion measurements in asymmetrically strained SiGe/Si superlattices. *Applied Physics Letters*, **1990**, 56, 2628-2630. 3.4 43

220	High-quality strain-relaxed SiGe alloy grown on implanted silicon insulator substrate. <i>Applied Physics Letters</i> , 2000 , 76, 2680-2682	3-4	42
219	Detection of magnetic resonance on photoluminescence from a Si/Si _{1-x} Ge _x strained-layer superlattice. <i>Physical Review Letters</i> , 1990 , 65, 1247-1250	7-4	42
218	Effect of resistance-area product on spin-transfer switching in MgO-based magnetic tunnel junction memory cells. <i>Applied Physics Letters</i> , 2011 , 98, 072512	3-4	41
217	Cross-plane thermal conductivity of self-assembled Ge quantum dot superlattices. <i>Physical Review B</i> , 2003 , 67,	3-3	40
216	Growth and characterization of molecular beam epitaxial GaAs layers on porous silicon. <i>Applied Physics Letters</i> , 1987 , 51, 814-816	3-4	40
215	High-quality strain-relaxed SiGe films grown with low temperature Si buffer. <i>Journal of Applied Physics</i> , 2001 , 89, 8279-8283	2-5	39
214	Boron surface segregation in silicon molecular beam epitaxy. <i>Applied Physics Letters</i> , 1988 , 53, 48-50	3-4	39
213	Nanoscale magnetic tunnel junction sensors with perpendicular anisotropy sensing layer. <i>Applied Physics Letters</i> , 2012 , 101, 062412	3-4	38
212	Temperature effect on the formation of uniform self-assembled Ge dots. <i>Applied Physics Letters</i> , 2003 , 83, 2847-2849	3-4	38
211	Compliant effect of low-temperature Si buffer for SiGe growth. <i>Applied Physics Letters</i> , 2001 , 78, 454-456	3-4	38
210	Normal incidence infrared detector using intervalence-subband transitions in Si _{1-x} Ge _x /Si quantum wells. <i>Applied Physics Letters</i> , 1992 , 61, 2434-2436	3-4	38
209	Electric-field-driven magnetization switching and nonlinear magnetoelasticity in Au/FeCo/MgO heterostructures. <i>Scientific Reports</i> , 2016 , 6, 29815	4-9	38
208	Enhancement of microwave emission in magnetic tunnel junction oscillators through in-plane field orientation. <i>Applied Physics Letters</i> , 2011 , 99, 032503	3-4	37
207	High-quality Ge films on Si substrates using Sb surfactant-mediated graded SiGe buffers. <i>Applied Physics Letters</i> , 2001 , 79, 3431-3433	3-4	37
206	Interband resonant tunneling in InAs/AlSb/GaSb symmetric polytype structures. <i>Physical Review B</i> , 1992 , 46, 16012-16017	3-3	37
205	Dependence of tunneling current on structural variations of superlattice devices. <i>Applied Physics Letters</i> , 1985 , 46, 167-168	3-4	37
204	Optical phonons in self-assembled Ge quantum dot superlattices: Strain relaxation effects. <i>Journal of Applied Physics</i> , 2002 , 92, 6804-6808	2-5	36
203	Intersubband transitions in a p-type delta -doped SiGe/Si quantum well. <i>Physical Review B</i> , 1993 , 47, 15638-15647	3-3	36

202	SiGe quantum dots prepared on an ordered mesoporous silica coated Si substrate. <i>Applied Physics Letters</i> , 1997 , 71, 2448-2450	3-4	35
201	SiGe band engineering for MOS, CMOS and quantum effect devices. <i>Journal of Materials Science: Materials in Electronics</i> , 1995 , 6, 311-324	2-1	35
200	Band X-state influences on resonant tunneling current in single- and double-barrier GaAs/AlAs structures. <i>Applied Physics Letters</i> , 1989 , 54, 1341-1343	3-4	35
199	Intersubband absorption in Sb doped Si/Si _{1-x} Ge _x quantum well structures grown on Si (110). <i>Applied Physics Letters</i> , 1992 , 60, 2264-2266	3-4	34
198	Uniformity and crystalline quality of CoSi ₂ /Si heterostructures grown by molecular beam epitaxy and reactive deposition epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1985 , 3, 596		34
197	Electric field control and effect of Pd capping on magnetocrystalline anisotropy in FePd thin films: A first-principles study. <i>Physical Review B</i> , 2014 , 89,	3-3	33
196	A novel technique for studying electric field effect of carrier emission from a deep level center. <i>Applied Physics Letters</i> , 1983 , 42, 838-840	3-4	32
195	Effect of channel doping on the low-frequency noise in GaN/AlGa _N heterostructure field-effect transistors. <i>Applied Physics Letters</i> , 1999 , 75, 2064-2066	3-4	31
194	Nanocrystalline Ge in SiO ₂ by annealing of GeSi _{1-x} O ₂ in hydrogen. <i>Applied Physics Letters</i> , 1993 , 62, 3321-3323	3-4	31
193	Nanometer-structure writing on Si(100) surfaces using a non-contact-mode atomic force microscope. <i>Applied Physics Letters</i> , 1994 , 65, 1415-1417	3-4	31
192	Transport study of a single bismuth nanowire fabricated by the silver and silicon nanowire shadow masks. <i>Applied Physics Letters</i> , 2006 , 89, 141503	3-4	30
191	Effective compliant substrate for low-dislocation relaxed SiGe growth. <i>Applied Physics Letters</i> , 2001 , 78, 1219-1221	3-4	30
190	Photoluminescence of hydrogenated Si _m Ge _n superlattices. <i>Applied Physics Letters</i> , 1991 , 59, 1705-1707	3-4	30
189	Observation of large Stark shift in GeSi _{1-x} /Si multiple quantum wells. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990 , 8, 217		30
188	The effect of phosphorus ion implantation on molybdenum/silicon contacts. <i>Journal of Applied Physics</i> , 1981 , 52, 4027-4032	2-5	30
187	Hole transport through minibands of a symmetrically strained GeSi _{1-x} /Si superlattice. <i>Applied Physics Letters</i> , 1989 , 54, 1564-1566	3-4	29
186	Observation of inter-sub-level transitions in modulation-doped Ge quantum dots. <i>Applied Physics Letters</i> , 1999 , 75, 1745-1747	3-4	28
185	One-dimensional transport in quantum well wire-high electron mobility transistor. <i>Applied Physics Letters</i> , 1986 , 49, 1738-1740	3-4	28

184	Investigation of flicker noise and deep-levels in GaN/AlGaIn transistors. <i>Journal of Electronic Materials</i> , 2000 , 29, 297-301	1.9	27
183	Growth and study of self-organized Ge quantum wires on Si(111) substrates. <i>Applied Physics Letters</i> , 1999 , 74, 2471-2473	3.4	27
182	An investigation on surface conditions for Si molecular beam epitaxial (MBE) growth. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1985 , 3, 1035-1039	2.9	27
181	Defect spatial distributions in annealed ion-implanted silicon measured by a transient capacitance technique. <i>Applied Physics Letters</i> , 1976 , 29, 700-702	3.4	27
180	Reduction of switching current density in perpendicular magnetic tunnel junctions by tuning the anisotropy of the CoFeB free layer. <i>Journal of Applied Physics</i> , 2012 , 111, 07C907	2.5	26
179	Molecular beam epitaxial growth of CoSi ₂ on porous Si. <i>Applied Physics Letters</i> , 1987 , 51, 1809-1811	3.4	26
178	Growth and characterization of Ge/Si strained-layer superlattices. <i>Applied Physics Letters</i> , 1988 , 53, 1835-1837	3.4	25
177	Electric-field-induced thermally assisted switching of monodomain magnetic bits. <i>Journal of Applied Physics</i> , 2013 , 113, 013912	2.5	24
176	NONVOLATILE SPINTRONICS: PERSPECTIVES ON INSTANT-ON NONVOLATILE NANOELECTRONIC SYSTEMS. <i>Spin</i> , 2012 , 02, 1250009	1.3	24
175	Demonstration of Si homojunction far-infrared detectors. <i>Applied Physics Letters</i> , 1998 , 72, 2307-2309	3.4	24
174	Spin-wave utilization in a quantum computer. <i>Physical Review A</i> , 2001 , 64,	2.6	24
173	Photoluminescence and optically detected magnetic resonance of Si/Si _{1-x} Ge _x strained-layer superlattices grown by molecular-beam epitaxy. <i>Physical Review B</i> , 1993 , 47, 1305-1315	3.3	24
172	Strain relief of metastable GeSi layers on Si(100). <i>Journal of Applied Physics</i> , 1994 , 75, 4475-4481	2.5	24
171	Boron oxide interaction with silicon in silicon molecular beam epitaxy. <i>Applied Physics Letters</i> , 1986 , 49, 847-849	3.4	24
170	A transient optical reflectivity study of laser annealing of ion-implanted silicon: Thresholds and kinetics. <i>Applied Physics Letters</i> , 1979 , 34, 363-365	3.4	24
169	Two dimensional crystal tunneling devices for THz operation. <i>Applied Physics Letters</i> , 2012 , 101, 263112	3.4	23
168	Nanostructure and temperature-dependent photoluminescence of Er-doped Y ₂ O ₃ thin films for micro-optoelectronic integrated circuits. <i>Journal of Applied Physics</i> , 2006 , 100, 073512	2.5	23
167	Selective Etching of SiGe on SiGe / Si Heterostructures. <i>Journal of the Electrochemical Society</i> , 1991 , 138, 202-204	3.9	22

166	Studies of molecular-beam epitaxy growth of GaAs on porous Si substrates. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988 , 6, 696		22
165	100-n-wide silicon-on-insulator structures by Si molecular beam epitaxy growth on porous silicon. <i>Applied Physics Letters</i> , 1986 , 48, 1793-1795	3-4	22
164	Optical properties of Y2O3 thin films doped with spatially controlled Er3+ by atomic layer deposition. <i>Journal of Applied Physics</i> , 2007 , 101, 123116	2.5	21
163	Interface properties of thin oxides grown on strained GexSi1-x layer. <i>Journal of Applied Physics</i> , 1994 , 76, 982-986	2.5	21
162	Intersubband infrared absorption in GexSi1-x/Si superlattice by photocurrent measurement. <i>Applied Physics Letters</i> , 1990 , 56, 1342-1344	3-4	21
161	Primary defects in low-fluence ion-implanted silicon. <i>Applied Physics Letters</i> , 1980 , 36, 48-50	3-4	21
160	Modification of the three-phonon Umklapp process in a quantum wire. <i>Applied Physics Letters</i> , 2001 , 79, 851-853	3-4	20
159	Infrared multispectral detection using Si/SixGe1-x quantum well infrared photodetectors. <i>Applied Physics Letters</i> , 2001 , 78, 495-497	3-4	19
158	Study of Si/GeSi p-n heterostructures. <i>Journal of Applied Physics</i> , 1991 , 69, 6674-6678	2.5	19
157	Si/GexSi1-x/Si resonant tunneling diode doped by thermal boron source. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1989 , 7, 327		19
156	Enhancement of Si hole mobility in coupled delta-doped wells. <i>Applied Physics Letters</i> , 1993 , 62, 3455-3457	3-4	18
155	Quantum devices using SiGe/Si heterostructures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1991 , 9, 2064		18
154	Instability of a GexSi1-xO2 film on a GexSi1-x layer. <i>Journal of Applied Physics</i> , 1992 , 72, 4444-4446	2.5	18
153	X-ray studies of heat treated SiGe/Si strained-layer superlattices. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990 , 8, 254		18
152	Defects in Q-switched laser annealed silicon. <i>Journal of Applied Physics</i> , 1983 , 54, 3839-3848	2.5	18
151	Frequency and power limit of quantum well oscillators. <i>Applied Physics Letters</i> , 1986 , 48, 1003-1005	3-4	18
150	Induced interface interactions in Ti/Si systems by ion implantation. <i>Journal of Vacuum Science and Technology</i> , 1979 , 16, 130-133		18
149	Perpendicular magnetic tunnel junction with W seed and capping layers. <i>Journal of Applied Physics</i> , 2017 , 121, 153902	2.5	17

148	Tunable normal incidence Ge quantum dot midinfrared detectors. <i>Journal of Applied Physics</i> , 2004 , 96, 773-776	2.5	17
147	Growth of SiC film on Si substrate by surface reaction using hydrocarbon gas and Si molecular beams in ultrahigh vacuum. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992 , 10, 930		17
146	New silicon-on-insulator technology using a two-step oxidation technique. <i>Applied Physics Letters</i> , 1986 , 49, 1104-1106	3.4	17
145	Strain in epitaxial CoSi ₂ films on Si (111) and inference for pseudomorphic growth. <i>Applied Physics Letters</i> , 1989 , 55, 1874-1876	3.4	16
144	Insight into the antiferromagnetic structure manipulated by electronic reconstruction. <i>Physical Review B</i> , 2016 , 94,	3.3	16
143	SiGe resonant tunneling hot-carrier transistor. <i>Applied Physics Letters</i> , 1990 , 56, 1061-1063	3.4	15
142	In-plane magnetic field effect on switching voltage and thermal stability in electric-field-controlled perpendicular magnetic tunnel junctions. <i>AIP Advances</i> , 2016 , 6, 075014	1.5	15
141	Field-Free Switching of Perpendicular Magnetization through Voltage-Gated Spin-Orbit Torque 2019 ,		15
140	Formation of nanometer-scale InAs islands on silicon. <i>Journal of Electronic Materials</i> , 1999 , 28, 432-436	1.9	14
139	Temperature-dependent morphology of three-dimensional InAs islands grown on silicon. <i>Applied Physics Letters</i> , 1999 , 75, 1273-1275	3.4	14
138	Interfacial roughness scaling and strain in lattice mismatched Si _{0.4} Ge _{0.6} thin films on Si. <i>Applied Physics Letters</i> , 1995 , 67, 629-631	3.4	14
137	Oscillator strength for intersubband transitions in strained n-type Si _{1-x} Ge _x quantum wells. <i>Physical Review B</i> , 1992 , 46, 7682-7690	3.3	14
136	Study of CoSi ₂ /Si strained layers grown by molecular beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1987 , 5, 745		14
135	Interband optical transitions in GaAs-Ga _{1-x} Al _x As superlattices in an applied electric field. <i>Physical Review B</i> , 1987 , 35, 653-659	3.3	14
134	Influence of substrate type and quality on carrier mobility in graphene nanoribbons. <i>Journal of Applied Physics</i> , 2013 , 114, 053701	2.5	13
133	Far-infrared free-hole absorption in epitaxial silicon films for homojunction detectors. <i>Applied Physics Letters</i> , 1997 , 71, 515-517	3.4	13
132	Response to [Comment on Raman scattering from a self-organized Ge dot superlattice][Appl. Phys. Lett. 75, 3572 (1999)]. <i>Applied Physics Letters</i> , 1999 , 75, 3574-3575	3.4	13
131	Boron delta-doped Si metal semiconductor field-effect transistor grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 1363-1365	3.4	13

130	Free-electron density and transit time in a finite superlattice. <i>Journal of Applied Physics</i> , 1986 , 59, 2968-2970	2.5	13
129	Defect formation chemistry of EL2 center at $E_c - 0.83$ eV in ion-implanted gallium arsenide. <i>Journal of Applied Physics</i> , 1982 , 53, 8653-8662	2.5	13
128	Sb surfactant-mediated SiGe graded layers for Ge photodiodes integrated on Si. <i>Journal of Applied Physics</i> , 2006 , 99, 024504	2.5	12
127	Electron intersubband absorption in Ge/Si $_{1-x}$ Ge $_x$ quantum-well structures grown on Si (001) substrate. <i>Applied Physics Letters</i> , 1994 , 64, 1256-1258	3.4	12
126	Luminescence of strained Si $_{1-x}$ Ge $_x$ alloy layers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992 , 61, 2586-2588	3.4	12
125	Deep level defect study of molecular beam epitaxially grown silicon films. <i>Applied Physics Letters</i> , 1986 , 48, 287-289	3.4	12
124	Analog to Stochastic Bit Stream Converter Utilizing Voltage-Assisted Spin Hall Effect. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1343-1346	4.4	11
123	Fabrication of nanometer size photoresist wire patterns with a silver nanocrystal shadowmask. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 1425-1427	2.9	11
122	Dependence of damage and strain on the temperature of Si irradiation in epitaxial Ge $_{0.10}$ Si $_{0.90}$ films on Si(100). <i>Journal of Applied Physics</i> , 1995 , 77, 2329-2338	2.5	11
121	Observation of a large capacitive current in a double barrier resonant tunneling diode at resonance. <i>Applied Physics Letters</i> , 1994 , 64, 2276-2278	3.4	11
120	Studies of interdiffusion in GeSi $_n$ strained layer superlattices. <i>Journal of Electronic Materials</i> , 1990 , 19, 125-129	1.9	11
119	Detection sensitivity and spatial resolution of reverse-bias pulsed deep-level transient spectroscopy for studying electric field-enhanced carrier emission. <i>Journal of Applied Physics</i> , 1985 , 57, 1016-1021	2.5	11
118	Tunable Magnetoelastic Effects in Voltage-Controlled Exchange-Coupled Composite Multiferroic Microstructures. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 6752-6760	9.5	10
117	Boron delta doping in Si and SiGe and its application toward field-effect transistor devices. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994 , 12, 1203		10
116	The study of relaxation in asymmetrically strained Si $_{1-x}$ Ge $_x$ Si superlattices. <i>Journal of Electronic Materials</i> , 1991 , 20, 389-394	1.9	10
115	Temperature dependences of the E0 transitions in bulk Ge and a Ge-rich (Si) $_m$ /(Ge) $_n$ superlattice. <i>Physical Review B</i> , 1992 , 45, 1712-1718	3.3	10
114	Electronic transitions in a Si $_m$ Ge $_n$ strained monolayer superlattice measured by photoreflectance. <i>Applied Physics Letters</i> , 1990 , 56, 1498-1500	3.4	10
113	Intersubband Auger recombination in a superlattice. <i>Physical Review B</i> , 1988 , 37, 1328-1333	3.3	10

112	A system for measuring deep-level spatial concentration distributions. <i>Journal of Applied Physics</i> , 1982 , 53, 449-453	2.5	10
111	A Spintronic Voltage-Controlled Stochastic Oscillator for Event-Driven Random Sampling. <i>IEEE Electron Device Letters</i> , 2017 , 38, 281-284	4.4	9
110	Prospects for High Thermoelectric Figures of Merit in 2D Systems. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 478, 55		9
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